Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

NEW PRODUCT

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
30V	30mΩ @ V_{GS} = 10V	6.2A
	42mΩ @ V_{GS} = 4.5V	5.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

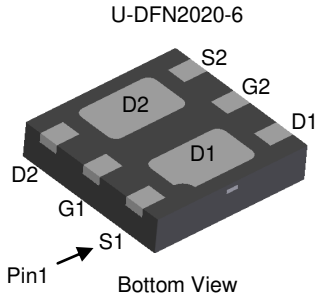
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

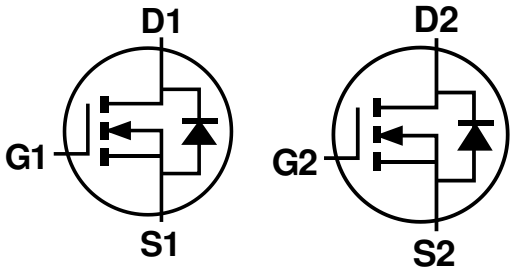
- Body Control Electronics
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3032LFDB-7	U-DFN2020-6	3,000/Tape & Reel
DMN3032LFDB-13	U-DFN2020-6	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6

N5 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: C = 2015)
M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +75°C	I_D	6.2 5.0	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	25	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	12	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	10	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	127	°C/W
	t<10s		75	
Total Power Dissipation (Note 6)		P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	72	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	1.0	µA	V_{DS} = 30V, V_{GS} = 0V
Zero Gate Voltage Drain Current T_J = +150°C (Note 9)	I_{DSS}	-	-	100	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	1.5	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	25 30	30 42	mΩ	V_{GS} = 10V, I_D = 5.8A V_{GS} = 4.5V, I_D = 4.8A
Diode Forward Voltage	V_{SD}	-	0.75	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	500	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	52	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	44	-	pF	
Gate Resistance	R_g	-	2.3	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	5.0	-	nC	V_{DS} = 15V, I_D = 5.8A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	10.6	-	nC	
Gate-Source Charge	Q_{gs}	-	1.3	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.8	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	2.2	-	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 2.6Ω, R_G = 3Ω
Turn-On Rise Time	t_R	-	2.6	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	9.7	-	ns	
Turn-Off Fall Time	t_F	-	2.0	-	ns	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

NEW PRODUCT

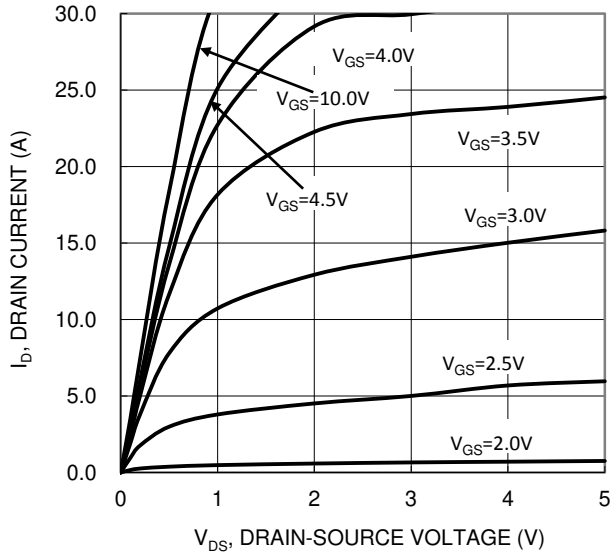


Figure 1. Typical Output Characteristic

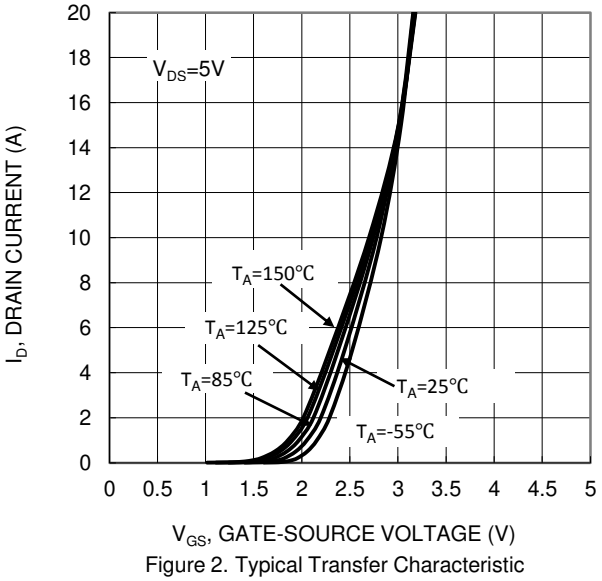


Figure 2. Typical Transfer Characteristic

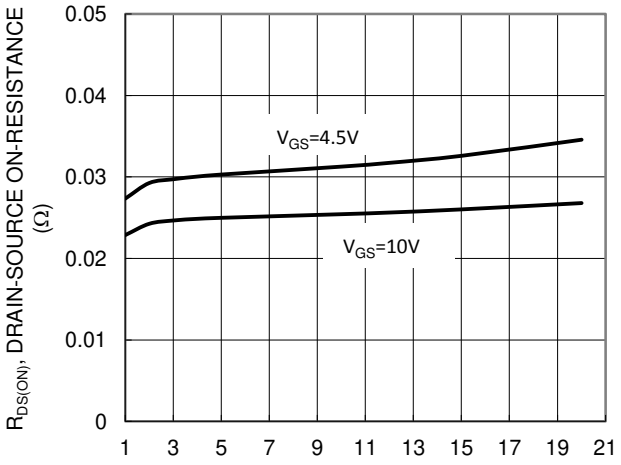


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

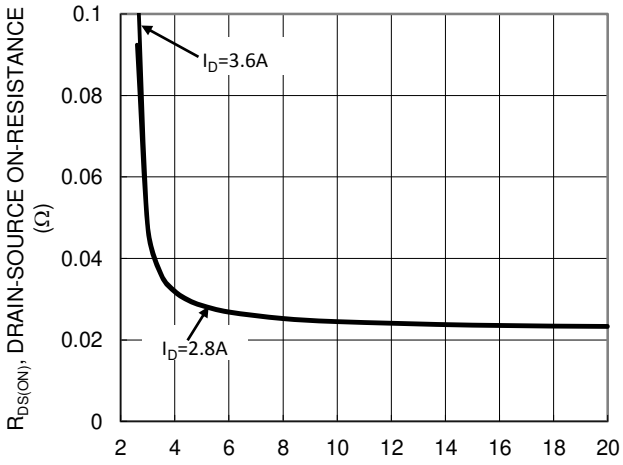


Figure 4. Typical Transfer Characteristic

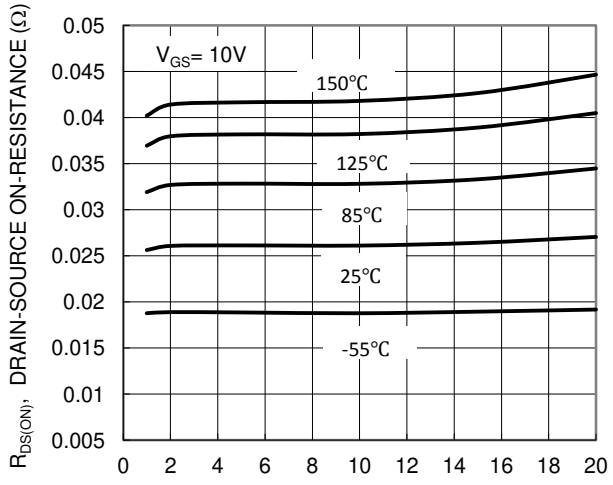


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

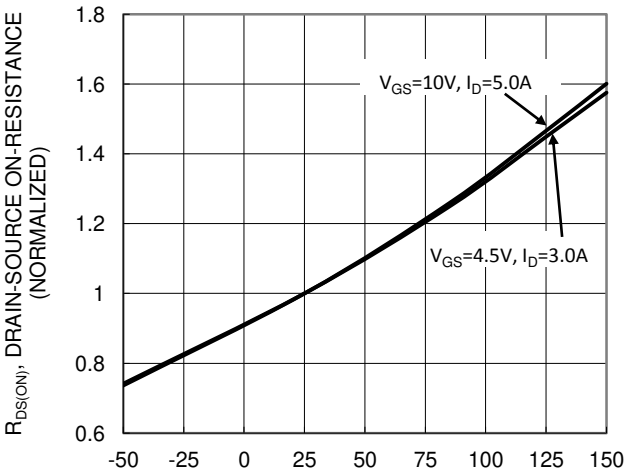


Figure 6. On-Resistance Variation with Temperature

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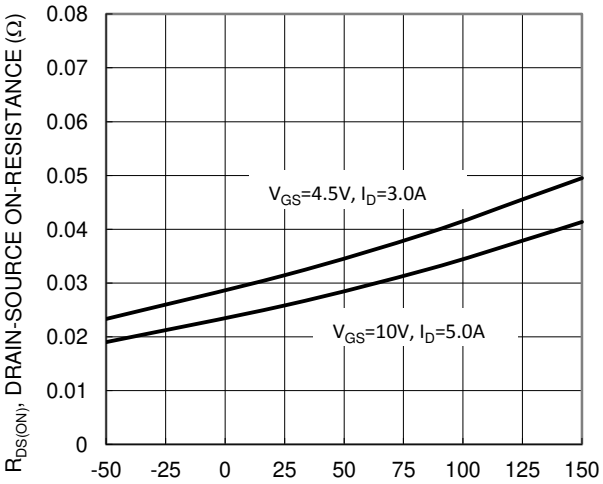

Figure 7. On-Resistance Variation with Temperature

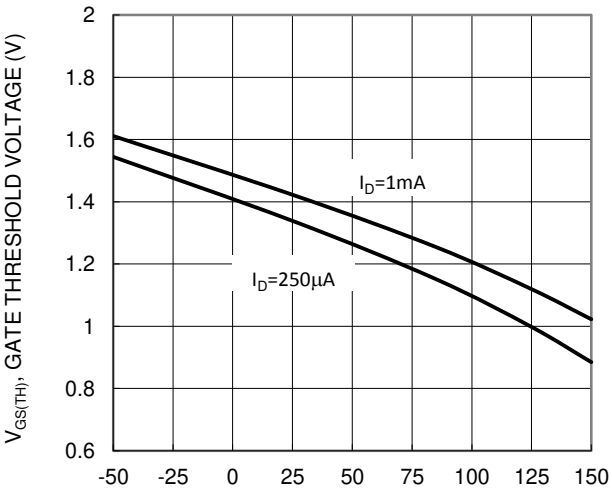

Figure 8. Gate Threshold Variation vs Junction Temperature

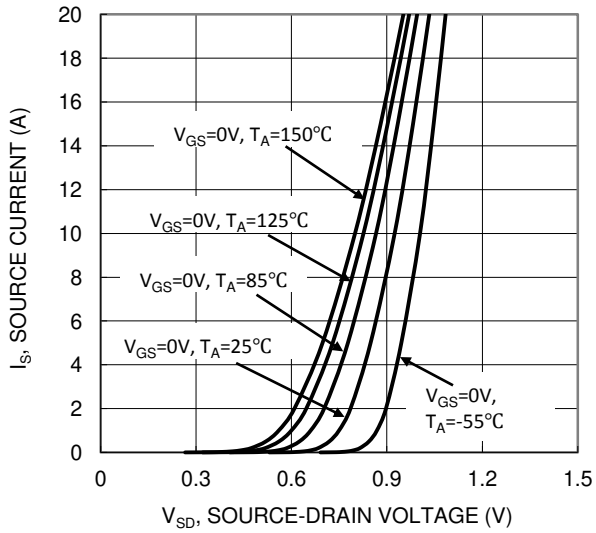

Figure 9. Diode Forward Voltage vs. Current

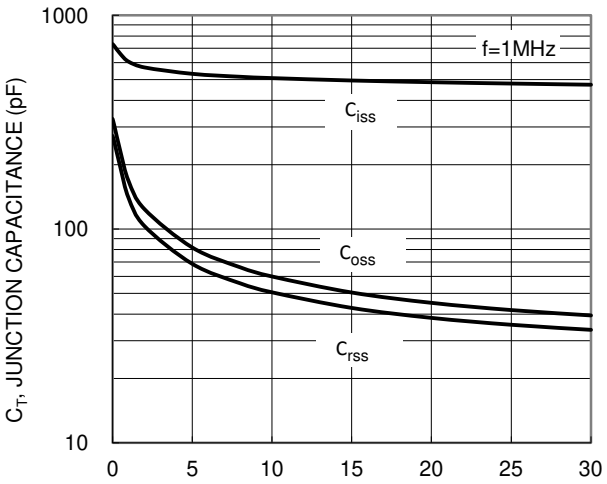

Figure 10. Typical Junction Capacitance

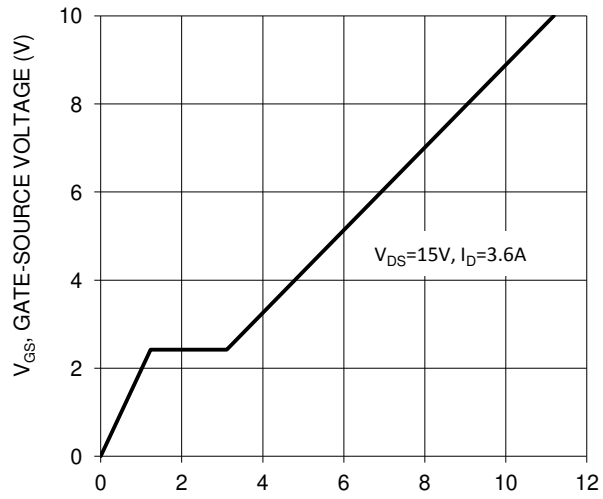

Figure 11. Gate Charge

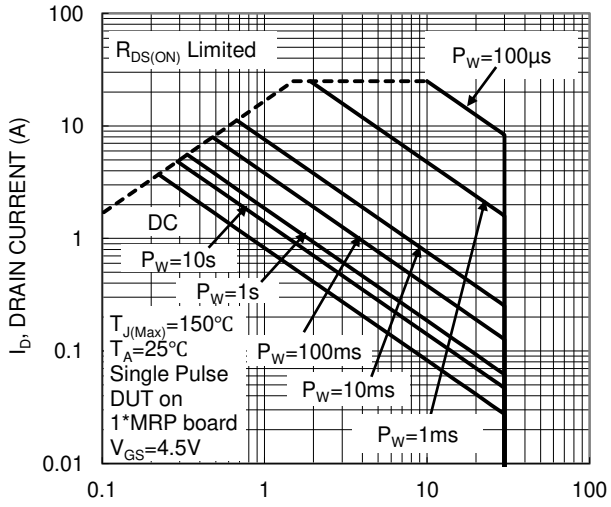

Figure 12. SOA, Safe Operation Area

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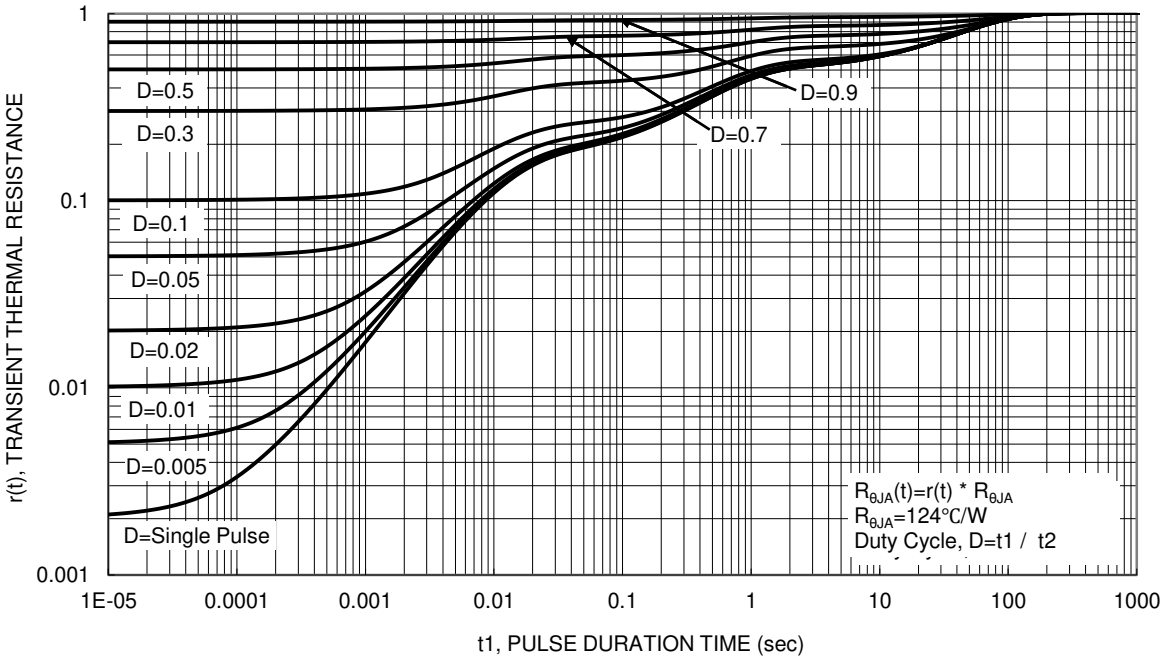
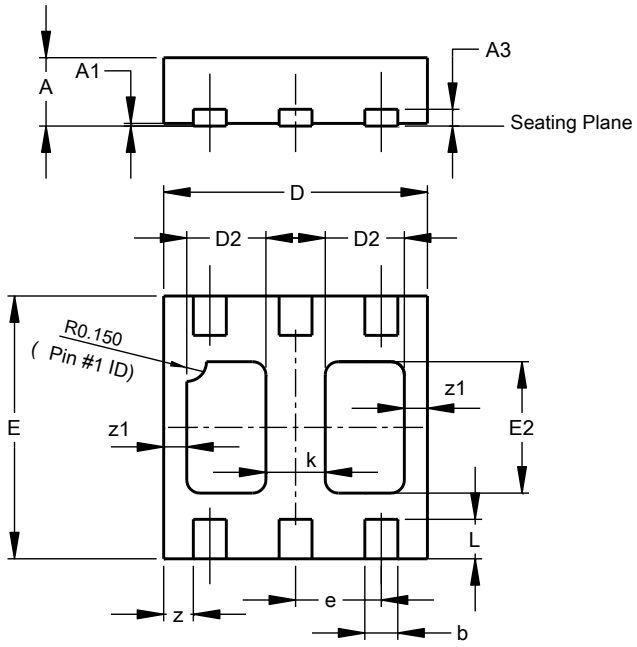


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

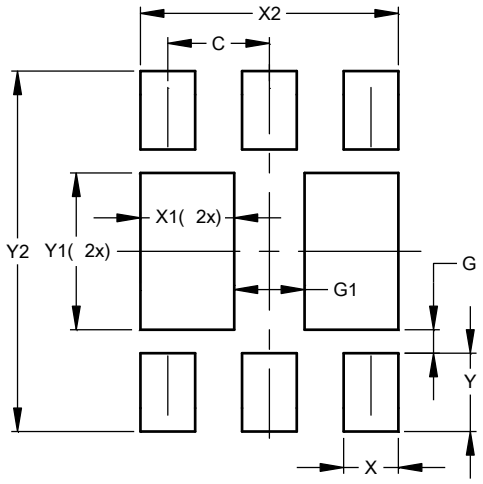


U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.15
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300